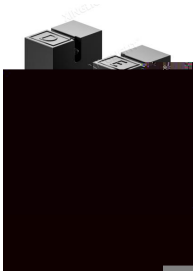
技术数据表



特点（C ）：

*

High reliability High radiant intensity Low forward voltage

*

Fast response time High photo sensitivity

* 940nm

Cut-off visible wavelength λp=940nm

* Rohs

Pb.Free RoHS compliant version

* MSL :2

Moisture sensitivity level MSL :2 levels

应用领域（P ）：

*

Slot machines

*

Small home appliances

*

Automatic Sensors

*

Fax machine

*

Scanner

目录

[redacted]

电性参数

✧极限参数 =25 ：Absolute Maximum Ratings (Temperature=25ÁC):

Input Emitter	Power Dissipation*1	PD	75	mW
	Continuous Forward Current	IF	50	mA
	Peak Forward Current*2	IF	1	A
	Reverse Voltage	VR	5	V
Output Detector	Power Dissipation*1	PD	75	mW
	- Collector-Emitter Voltage	VCEO	30	V
	- Emitter-Collector Voltage	VECO	5	V
	Collector Current	IC(on)	20	mA
Operating Temperature		Topr	-20~+85	
Storage Temperature		Tstg	-40~+85	
Lead Soldering Temperature*3		Tsol	260	

=25℃）：

Electro-Optical Charasteristics (

电压分档：

代码	最小值	最大值	单位	测试条件
R2-4	1.2	1.6	V	IF=20mA

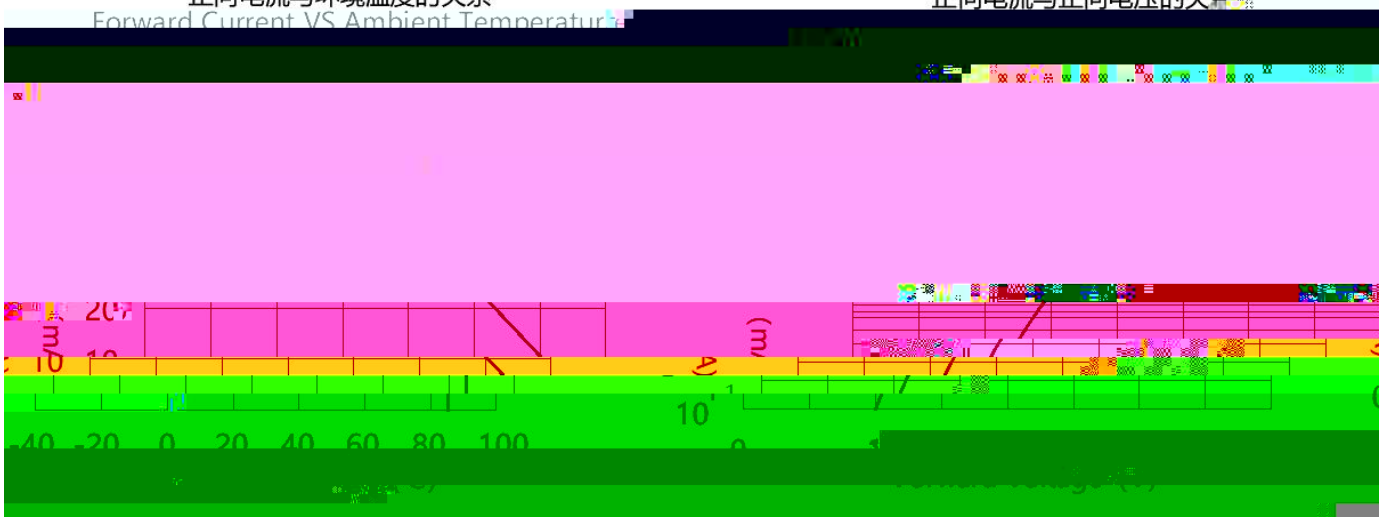
光电流分档：
Collector Current grading：

代码	最小值	最大值	单位	测试条件
IC27-39	8	20	mA	IF=20mA VCE=5V

典型特性曲线

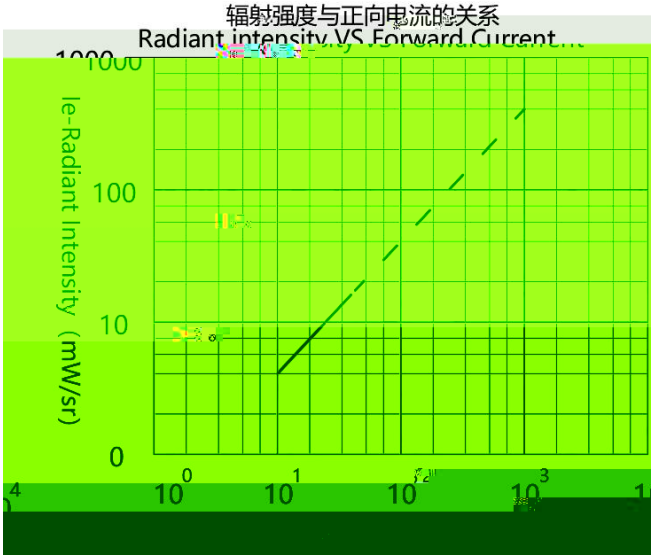
发射管特性曲线图 Typical Electro-Optical Characteristics Curves-IR

正向电流与环境温度的关系

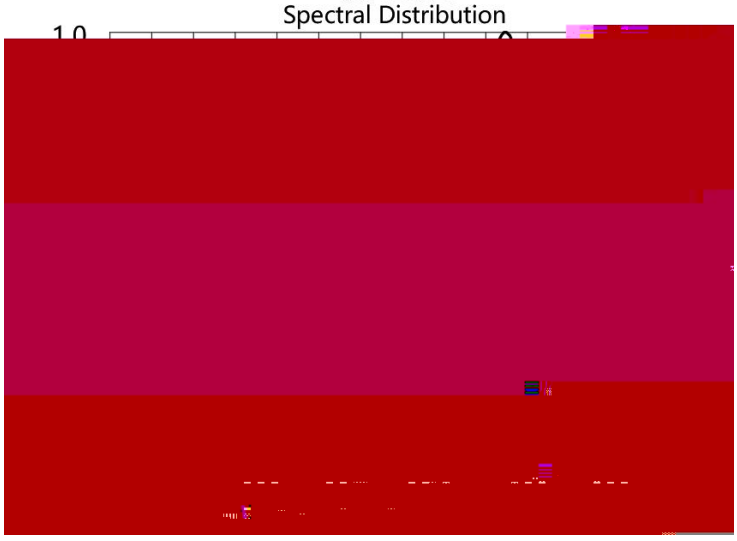


正向电流与正向电压的关系

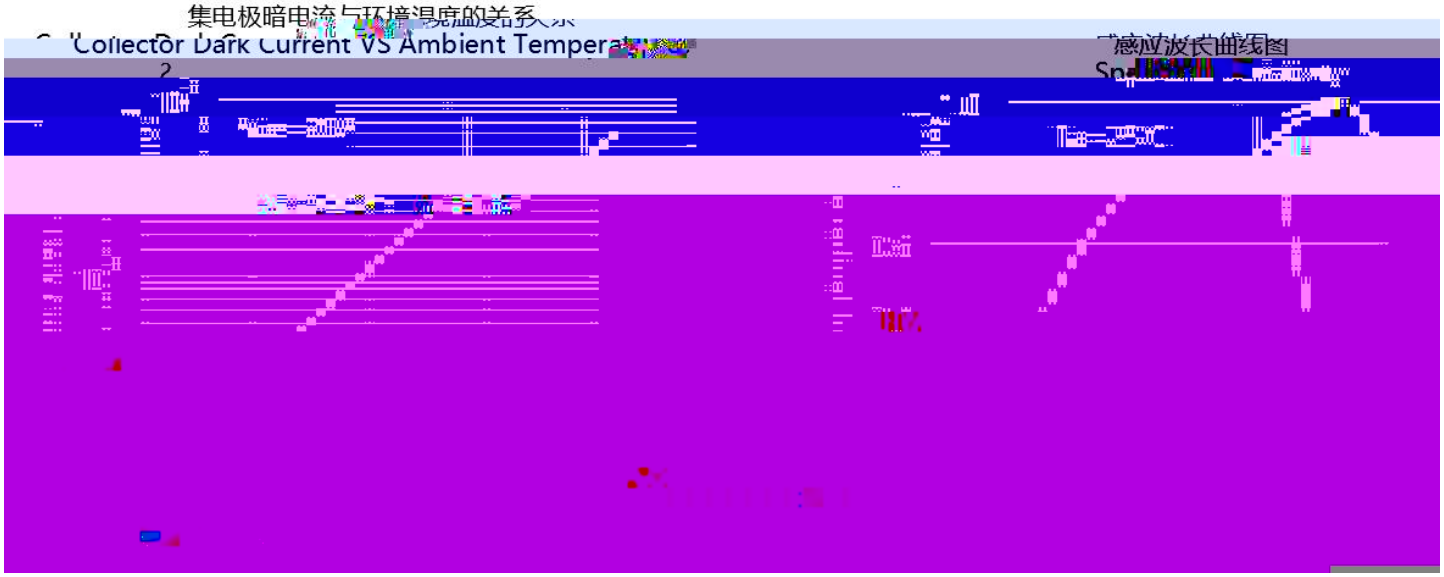
辐射强度与正向电流的关系

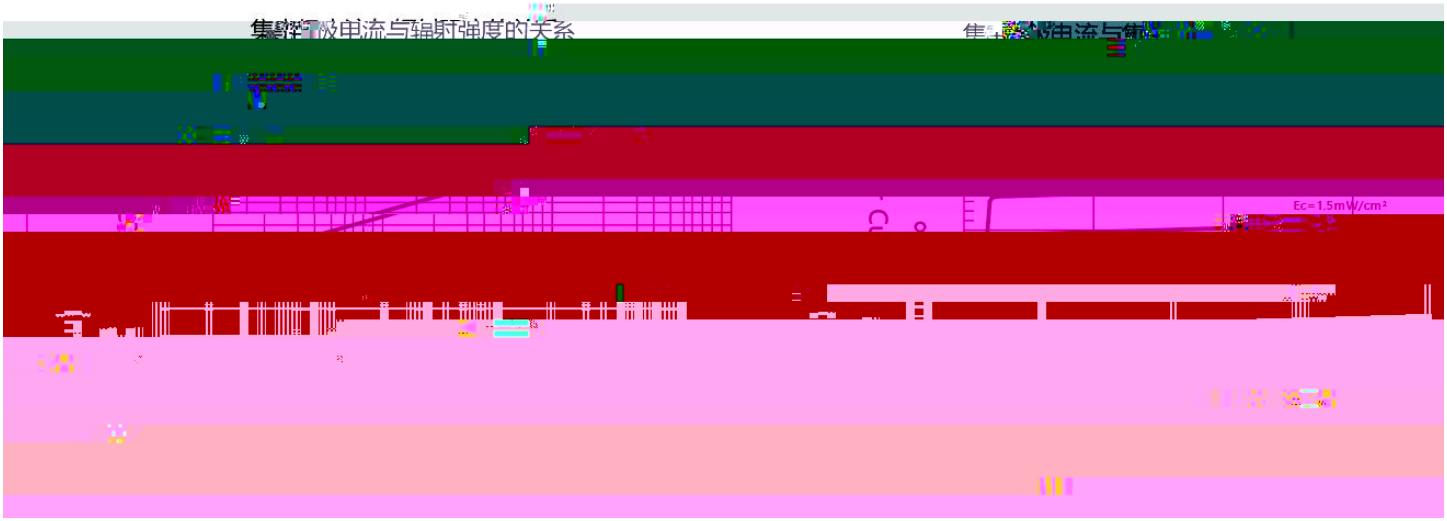


波长曲线图
Spectral Distribution



接收管特性曲线图 Typical Electro-Optical Characteristics Curves-PT





Part No. :[redacted]

外形尺寸

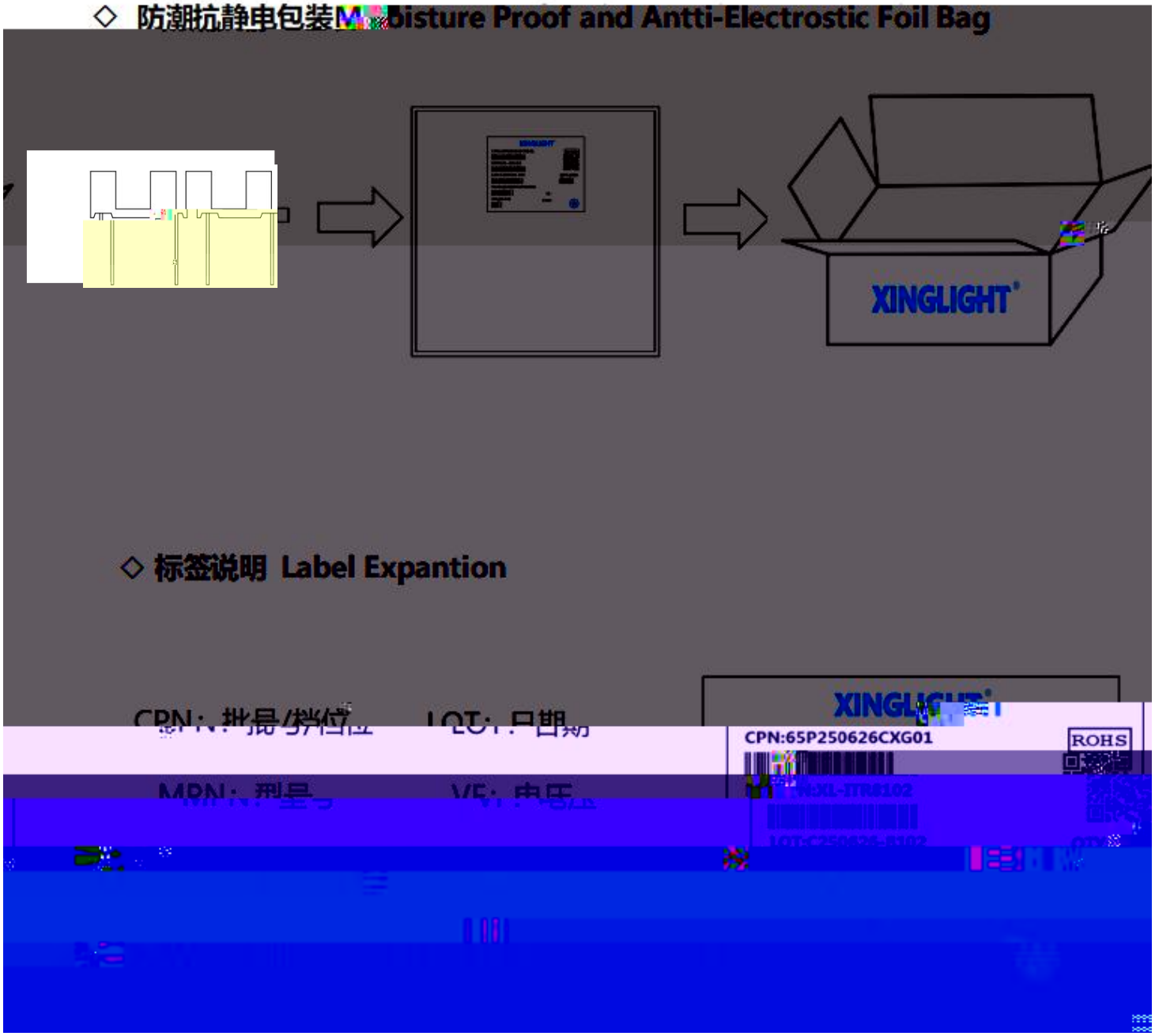
1. mm

Remarks: 1 Unit: mm

2. Ñ0.3mm

2. Tolerance: Ñ 0.3mm mn , ŭ ɤ

包装


◇ 防潮抗静电包装Moisture Proof and Antti-Electrostic Foil Bag

◇ 标签说明 Label Expantion

Part

使用注意事項

NPN

IR

IR PT

This product It is composed of infrared emission diode and NPN silicon photo transistor, which are packaged side by side in black On the converging optical axis in the thermoplastic shell. Photo transistor only receives radiation from IR. This is normal Condition. But when the object is in the middle, the photo transistor cannot receive radiation. For more component information, please Refer to IR and PT.